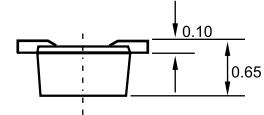
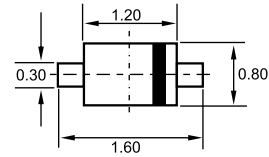




SOD-523



Dimensions in inches and (millimeters)

FEATURES

- High switching speed: max. 50 ns
- High continuous reverse voltage: 300 V
- Repetitive peak forward current: 625 mA
- Ultra small plastic SMD package.

APPLICATIONS

- High speed switching
- High voltage switching.

DESCRIPTION

The BAS521 is a high-voltage switching diode fabricated in planar technology and encapsulated in an ultra small SOD523 (SC-79) plastic SMD package.

PINNING

PIN	DESCRIPTION
1	cathode
2	anode

LIMITING VALUES

In accordance with the absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage		–	300	V
V_{RRM}	repetitive peak reverse voltage		–	300	V
I_F	continuous forward current	$T_s \leq 90\text{ }^\circ\text{C}$; note 1	–	250	mA
I_{FRM}	repetitive peak forward current	$t_p = 1\text{ ms}$; $\delta = 0.25$	–	1	A
I_{FSM}	non-repetitive peak forward current	$t_p = 1\text{ }\mu\text{s}$; square wave; $T_j = 25\text{ }^\circ\text{C}$ prior to surge	–	4.5	A
P_{tot}	total power dissipation	$T_s \leq 90\text{ }^\circ\text{C}$; note 1	–	500	mW
T_{stg}	storage temperature		–65	+150	$^\circ\text{C}$
T_j	junction temperature		–	150	$^\circ\text{C}$
T_{amb}	operating ambient temperature		–65	+150	$^\circ\text{C}$

Note

1. T_s is the temperature at the soldering point of the cathode tab.

ELECTRICAL CHARACTERISTICS
 $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{BR}	breakdown voltage	$I_R = 100\text{ }\mu\text{A}$	300	340	–	V
V_F	forward voltage	$I_F = 100\text{ mA}$; note 1	–	0.95	1.1	V
I_R	reverse current	$V_R = 250\text{ V}$	–	30	150	nA
		$V_R = 250\text{ V}$; $T_a = 150\text{ }^{\circ}\text{C}$	–	40	100	μA
t_{rr}	reverse recovery time	when switched from $I_F = 30\text{ mA}$ to $I_R = 30\text{ mA}$; $R_L = 100\text{ }\Omega$; measured at $I_R = 3\text{ mA}$	–	16	50	ns
C_d	diode capacitance	$V_R = 0\text{ V}$; $f = 1\text{ MHz}$	–	0.4	5	pF

Note

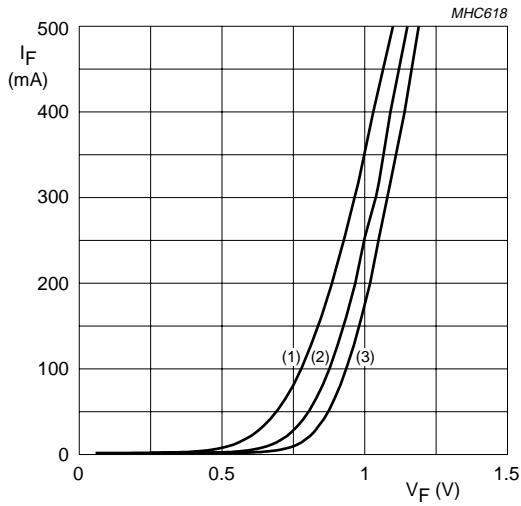
1. Pulse test: $t_p = 300\text{ }\mu\text{s}$; $\delta = 0.02$.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to solder point	note 1	120	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 2	500	K/W

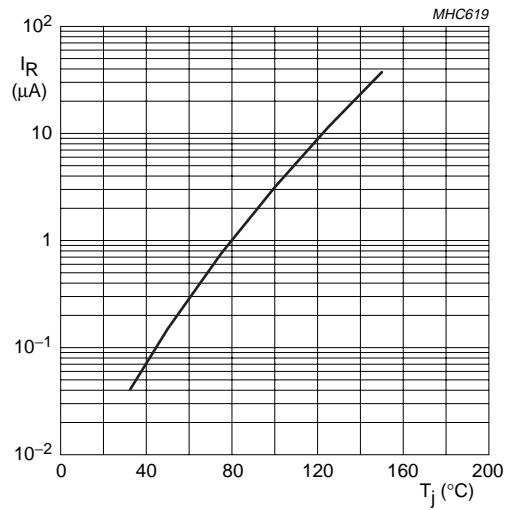
Notes

1. Soldering point of the cathode tab.
2. Refer to SOD523 (SC-79) standard mounting conditions.

GRAPHICAL DATA


- (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$.
- (2) $T_{amb} = 75\text{ }^{\circ}\text{C}$.
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.2 Forward current as a function of forward voltage; typical values.



$V_R = V_{Rmax}$; typical values.

Fig.3 Reverse current as a function of junction temperature.

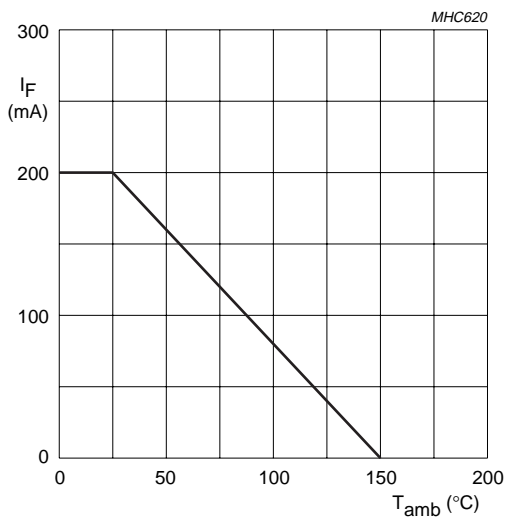


Fig.4 Maximum permissible continuous forward current as a function of ambient temperature.

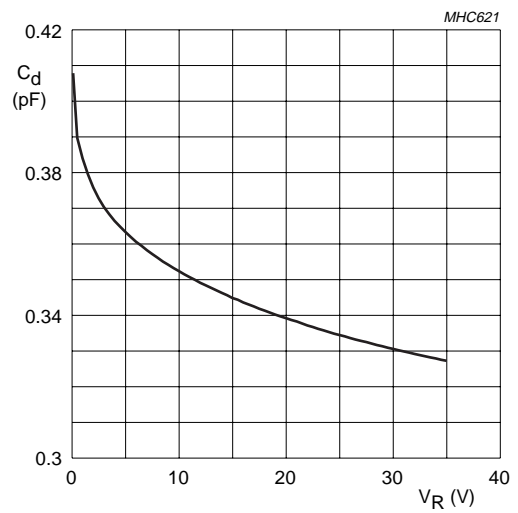
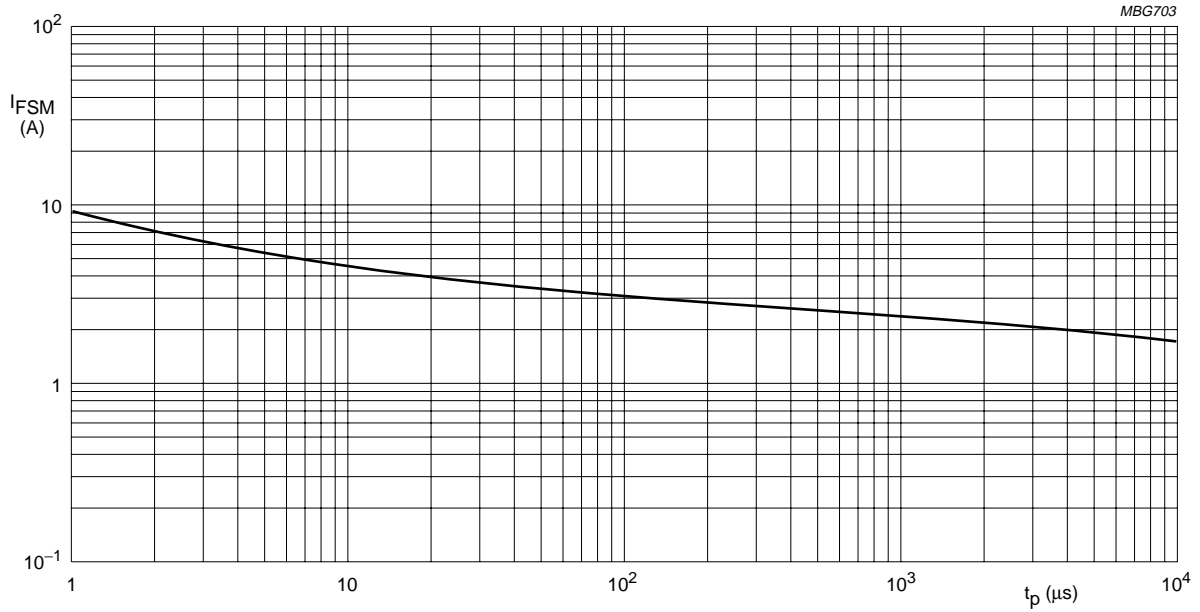


Fig.5 Diode capacitance as a function of reverse voltage; typical values.



Based on square wave currents.
 $T_j = 25^\circ C$ prior to surge.

Fig.6 Maximum permissible non-repetitive peak forward current as a function of pulse duration.